2SK4087LS

ON Semiconductor®

N-Channel Power MOSFET 600V, 14A, 610mΩ, TO-220F-3FS

http://onsemi.com

Features

- ON-resistance RDS(on)= 0.47Ω (typ.)
- · 10V drive

• Input capacitance Ciss=1200pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		600	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	14	Α
	I _{Dpack} *2	Tc=25°C (Our ideal heat dissipation condition)*3	9.2	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	52	Α
Allowable Power Dissipation	D=		2.0	W
	PD	Tc=25°C (Our ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		106	mJ
Avalanche Current *5	IAV		14	Α

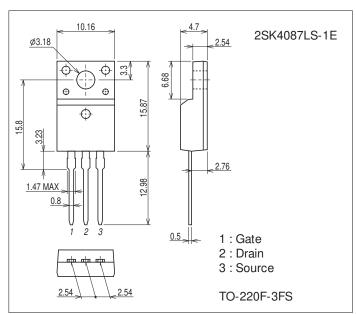
^{*1} Shows chip capability.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7528-001



Product & Package Information

• Package : TO-220F-3FS

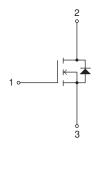
• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection





^{*2} Package limited.

^{*3} Our condition is radiation from backside.

^{*4} V_{DD}=50V, L=1mH, I_{AV}=14A (Fig.1)

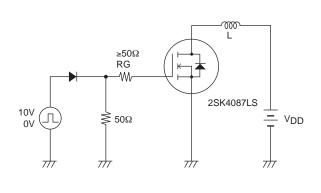
^{*5} L≤1mH, Single pulse

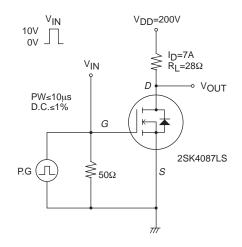
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Syllibol	Conditions	min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =480V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =7A	4	8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =7A, V _{GS} =10V		0.47	0.61	Ω
Input Capacitance	Ciss			1200		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		220		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	td(on)			27		ns
Rise Time	t _r	San Fig 0		72		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		144		ns
Fall Time	tf			48		ns
Total Gate Charge	Qg			46		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =14A		8.6		nC
Gate-to-Drain "Miller" Charge	Qgd			26.4		nC
Diode Forward Voltage	V _{SD}	I _S =14A, V _{GS} =0V		0.95	1.3	V

Fig.1 Unclamped Inductive Switching Test Circuit

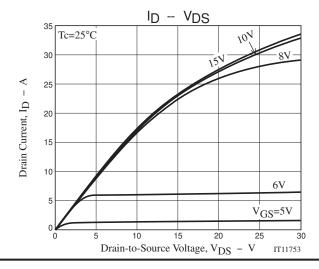
Fig.2 Switching Time Test Circuit

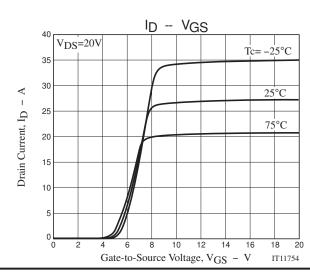


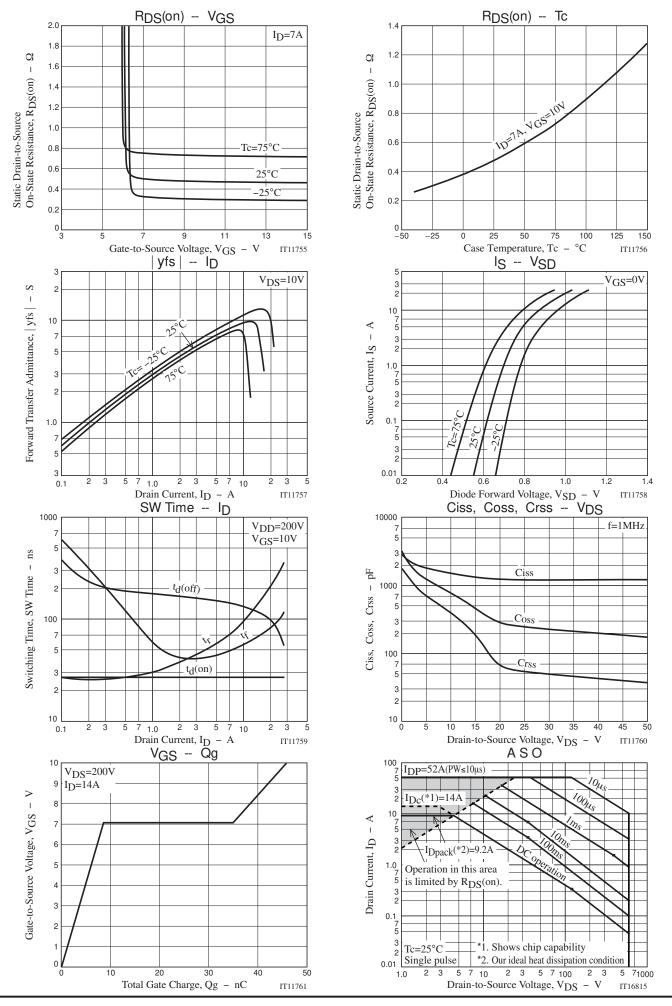


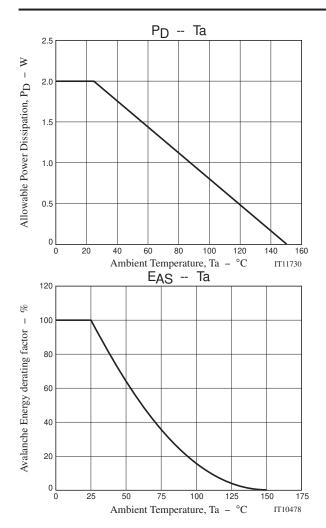
Ordering Information

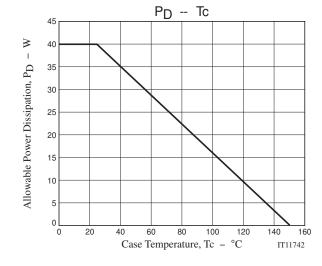
Device	Package	Shipping	memo
2SK4087LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free









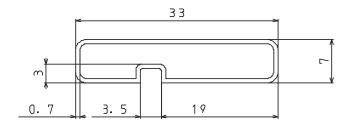


Magazine Specification

2SK4087LS-1E

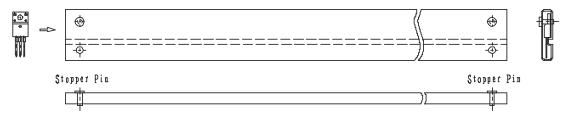
1. Packing Format

Package Name	Magazine Name	I 4.55		Maximum Number of devices contained (pcs)			Packing format		
1 4 4 4 4 4 1 4 4 4 4	Idag as the Hams	l	Inner box	Outer box	Inner BOX	Outer BOX			
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178			



Tolerance=±0.3mm
Thickness=0.7±0,2mm
Length =532.5±2mm
Material =PVC (Antistatic treatment)

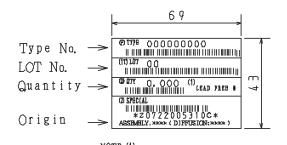
3. Storage method to magazine

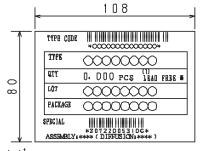


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



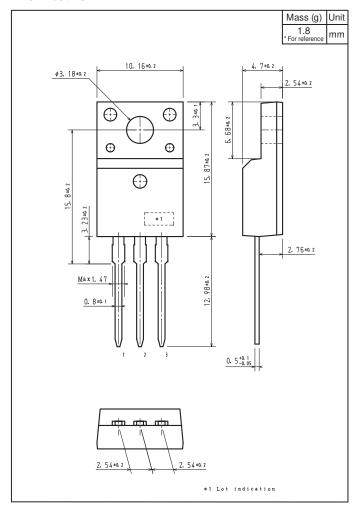


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

2SK4087LS-1E



Note on usage: Since the 2SK4087LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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